

First Named

Inventor : Baowei KANG

Appln. No. : 10/017,734

Filed : December 18, 2001

Title : POWER SEMICONDUCTOR SWITCHING
DEVICES WITH LOW POWER LOSS AND
METHOD FOR FABRICATING THE SAME

Docket No. : B784.312-1

Group Art Unit: 2823

Examiner: Khiem D. Nguyen

INFORMATION DISCLOSURE STATEMENT

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The enclosed PTO Form-1449 lists patents and publications submitted pursuant to 37 C.F.R. 1.97.

Copies of the patents or publications are enclosed as necessary.

TIME OF FILING

The Information Disclosure Statement is being filed:

1. X with the application or within three months of the filing date of a national application (other than a continued prosecution application under 37 C.F.R. 1.53(d)) or date of entry into the national stage of an international application or, to the best of the undersigned's knowledge, before the mailing date of a first Office action on the merits or a first office action after the filing of a request for continued examination under 37 C.F.R. 1.114, whichever event occurs last. In accordance with 37 C.F.R. 1.97(b), no certification or fee is required.

2. after the time period specified in paragraph 1 above, but, to the best of the undersigned's knowledge, before the mailing date of a final action under 37 C.F.R. 1.113 or notice of allowance under 37 C.F.R. 1.311, or an action that otherwise closes prosecution of the application. In accordance with 37 C.F.R. 1.97(c), submitted herewith is:

(check either A or B below)

- A. a statement as specified in 37 C.F.R. 1.97(e), no fee is required.
- B. the fee set forth in 37 C.F.R. 1.17(p) for submission of an Information Disclosure Statement under 37 C.F.R. 1.97(c).

Respectfully submitted,

KINNEY & LANGE, P.A.

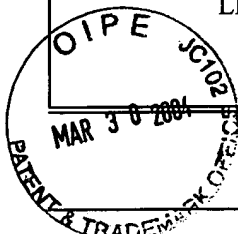
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3/30/04

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AMK:amh

FORM PTO-1449	Atty. Docket No.: B784.312-1	Application No.: 10/017,734
 <p>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</p>	First Named Inventor: Baowei KANG	
	Filing Date: December 18, 2001	Group Art: 2823

U.S. PATENT DOCUMENTS

Examiner Initials	Document No.	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents
AA			
AB			
AC			
AD			
AE			
AF			
AG			

FOREIGN PATENT DOCUMENTS

	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Translation Yes No
AH				
AI				

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AJ	Zohta, Yasuhito et al., "Shallow Donor State Produced by Proton Bombardment of Silicon", <i>Japan J. Appl. Phys.</i> 10, 1971, 532-533.
AK	Gorelkinskii, Yu and Nevinnyui, N.N., "Reversible Transformation of Defects in Hydrogen-Implanted Silicon", <i>Nuclear Instruments and Methods</i> 209/210, 1983, 677-682.
AL	Ntsoenzok, E. et al., "Study of the Defects Induced in N-Type Silicon Irradiated by 1-3 MeV Protons", <i>IEEE Transactions of Nuclear Science</i> , Vol. 41, No. 6, December 1994, 1932-1936.
AM	Ntsoenzok, E. et al., "Evolution of Shallow Donors with Proton Fluence in N-Type Silicon", <i>J. appl. Phys.</i> 79(11), June 1, 1996, 8274-8277.
AN	S. Godey et al., "Effect of Shallow Donors Induced by Hydrogen on P+N Junctions", <i>Materials Science & Engineering B58</i> , 1999, 108-112.

EXAMINER:

DATE CONSIDERED:

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.